

# SIGNATURES OF ATOMIC- SCALE STRUCTURE IN THE PROPERTIES OF SI QD QUBITS

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# INTRODUCTION

## BUILDING A QUANTUM COMPUTER

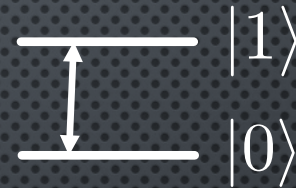
- WHY BUILD A QC? EFFICIENCY
  - INFORMATION SECURITY. SHOR ALGORITHM FOR PRIME FACTORIZATION. QUANTUM CRYPTOGRAPHY.
  - DATABASE SEARCH. GROVER ALGORITHM.
  - QUANTUM SIMULATIONS.
  - FOR THE FUN OF IT



# INTRODUCTION

## THE DIVINCENZO CRITERIA

- SCALABLE WELL-DEFINED QUBITS
- INITIALIZATION OF STATES
- UNIVERSAL QUANTUM GATES
- QUBIT-SPECIFIC MEASUREMENT
- LONG COHERENCE TIMES

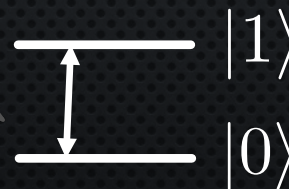


$|000\dots 0\rangle$

$\vec{\sigma}$        $U_{\text{CNOT}}$

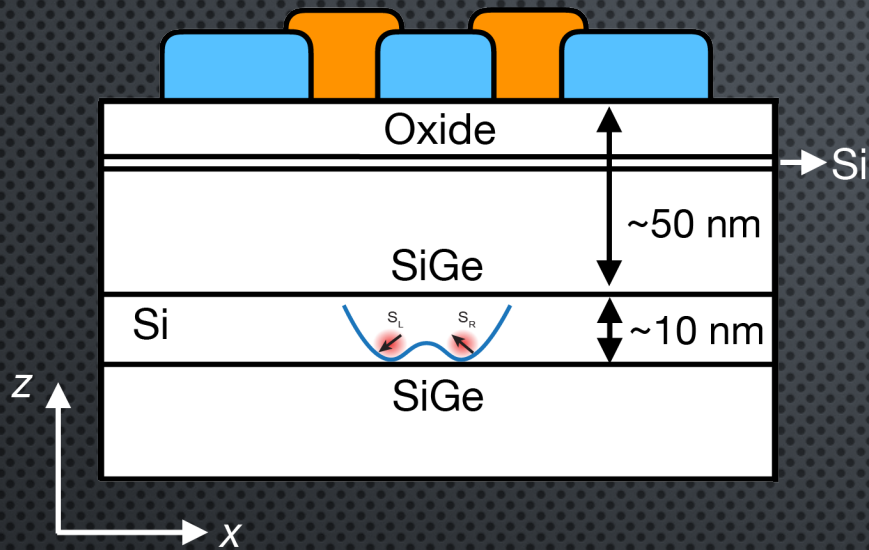
$|0\rangle$

$|1\rangle$

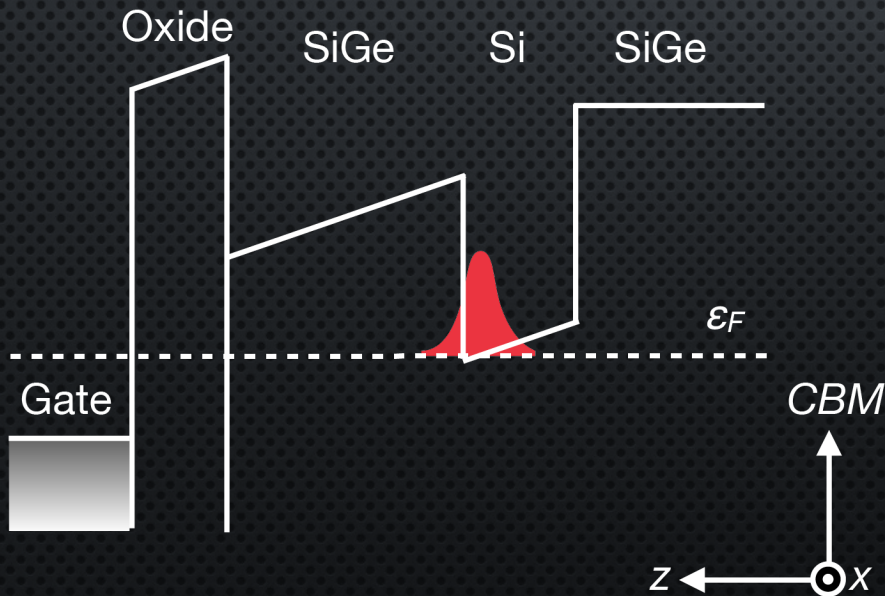




# SI/SiGe QUANTUM DOT QUBITS



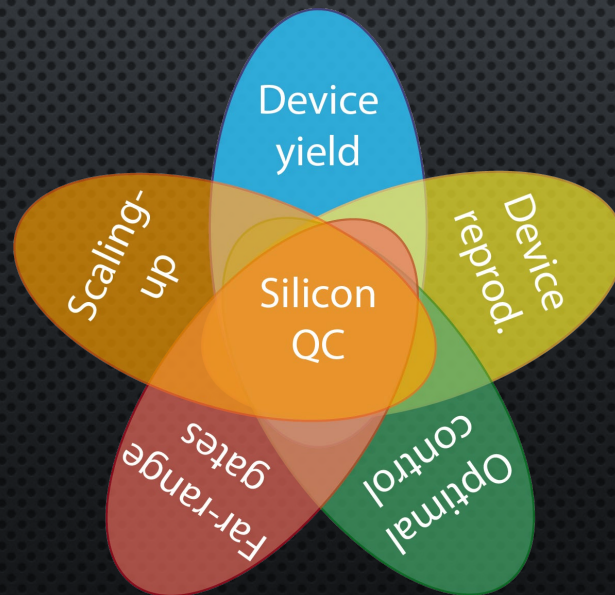
- Electrons/holes are confined in the Si quantum well
- The electron/hole is pushed against the interface
- Top gates are used to manipulate the qubit parameters
- Readout: spin-to-charge conversion





# STATUS AND CHALLENGES

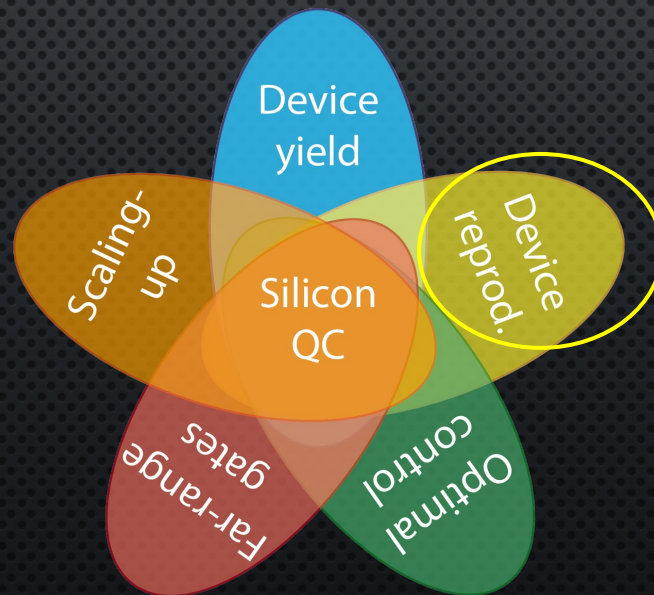
Metric	Spin	Orbital
$T_2^*$ ( $\mu\text{s}$ )	113 [Yoneda et al., Nature Nano 13, 102–106 (2018)]	0.157 [Thorgrimsson et al., npj Quantum Inf.3, 32 (2017)]
$F_{\text{single}}$ (%)	99.96 [Yang et al., Nature 580, 350-354 (2020)]	93 [Kim et al., npj Quantum Inf.1, 15004 (2015)]
$F_{\text{2-qubit}}$ (%)	98 [Huang et al., Nature 569, 532(2019)]	68 [Li et al., Nat. Commun.6, 7681 (2015)]





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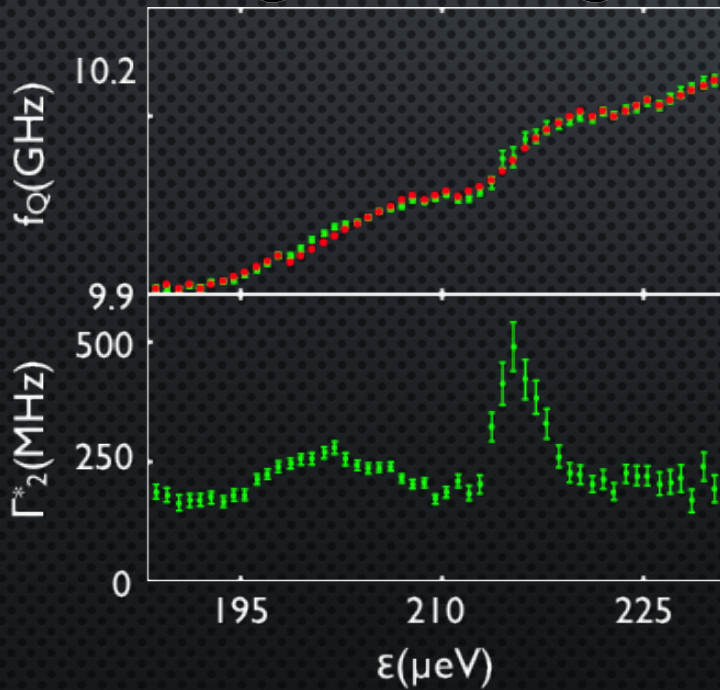
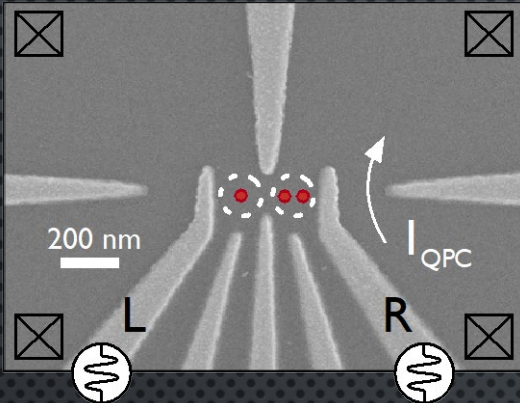
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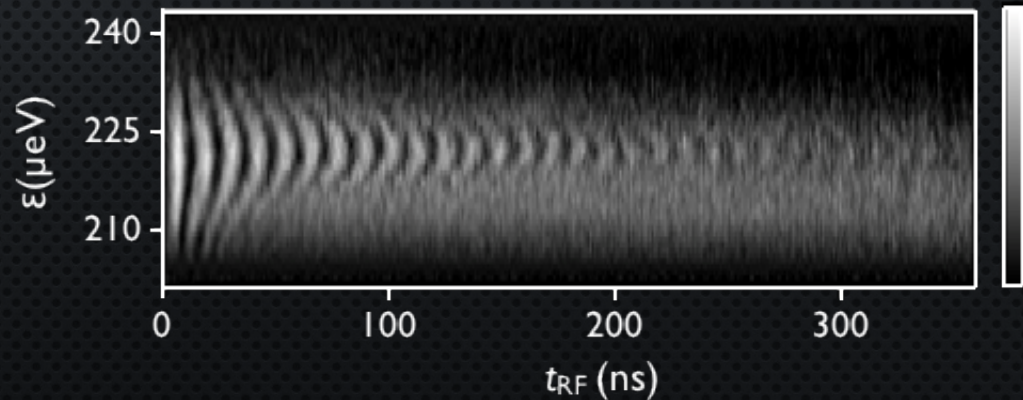
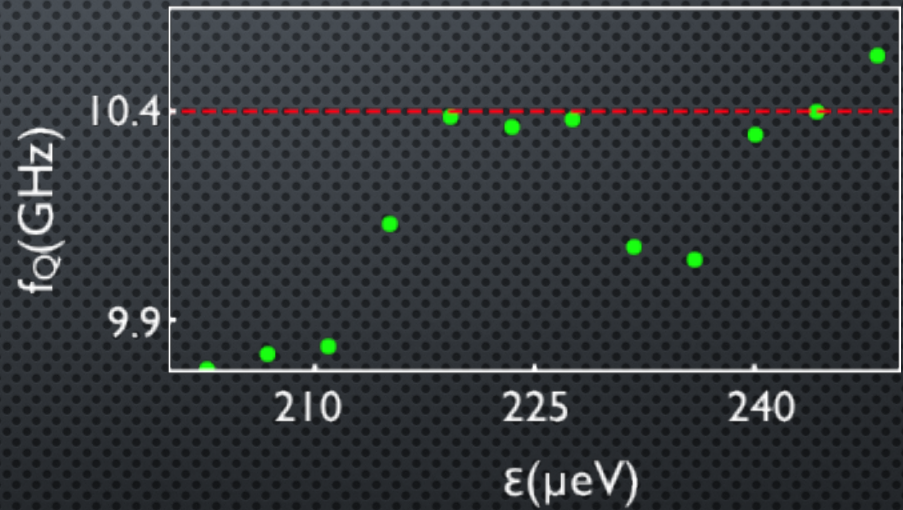
Valley physics  
Spin-orbit coupling  
Tunnel couplings  
Noise sources



# ANOMALOUS EXPERIMENTAL RESULTS

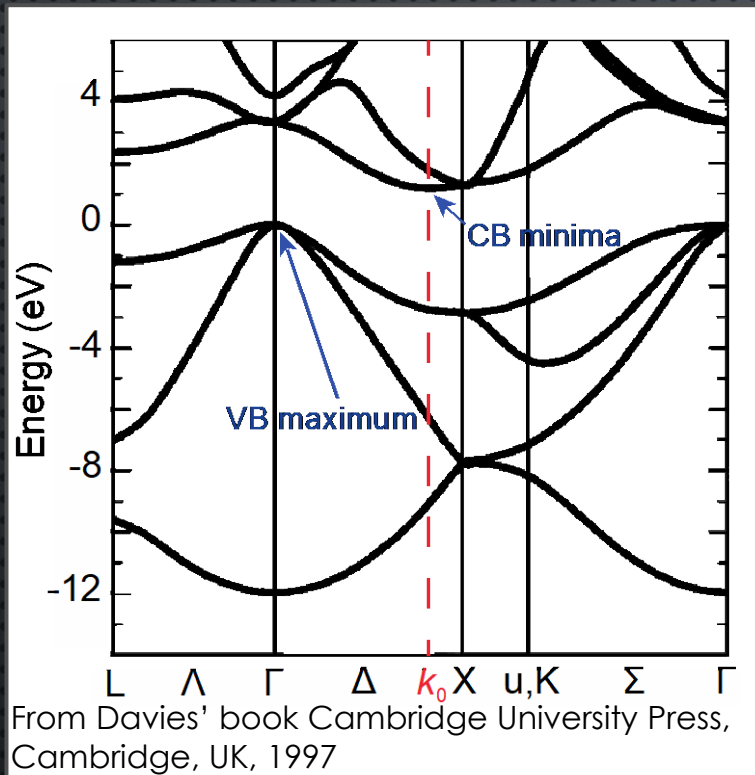


$$T_2^* \propto \left( \frac{dE}{d\epsilon} \right)^{-1}$$





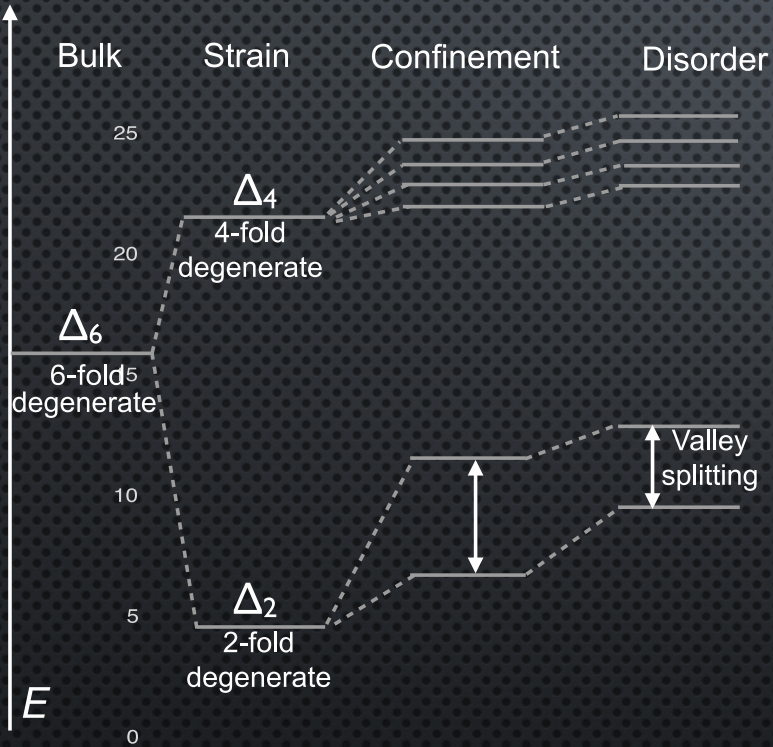
# THE VALLEY ISSUE (OR ADVANTAGE)



- At low temperatures, the confined electrons inherit the behavior from the conduction band minima:
- 6-fold degenerate valley states
- Leakage channel

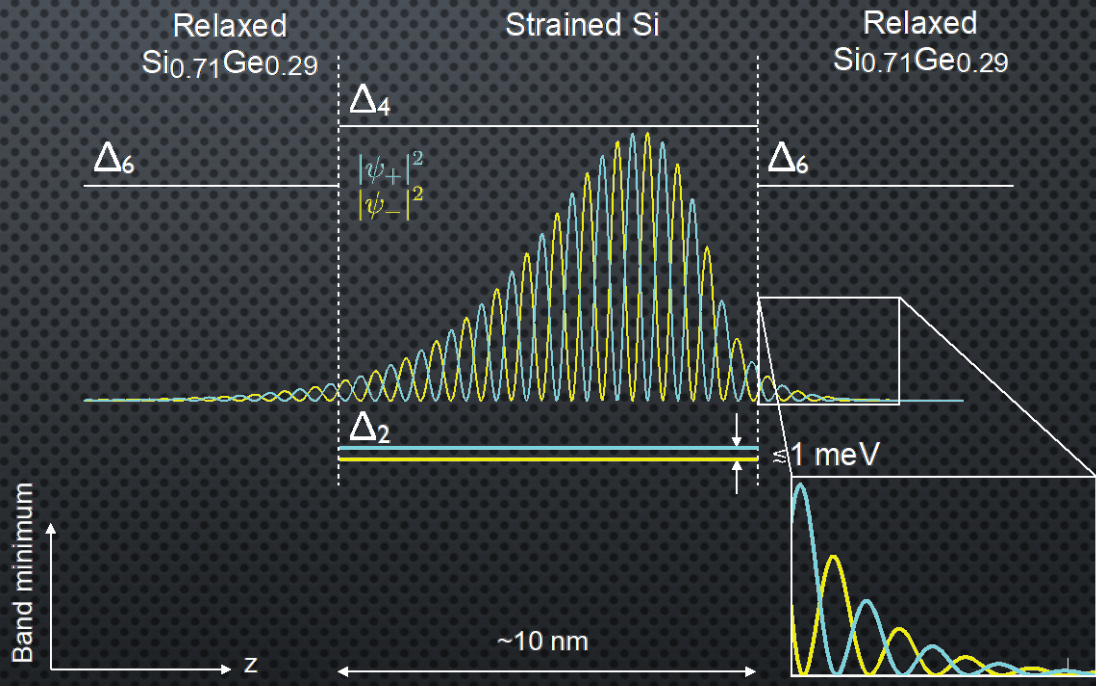
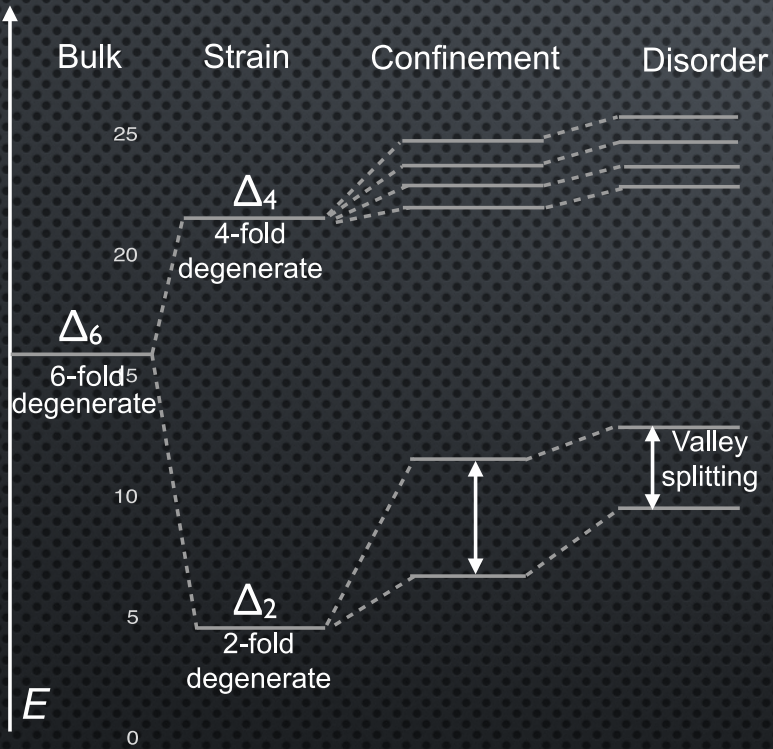


# VALLEY PHYSICS: ORIGINS



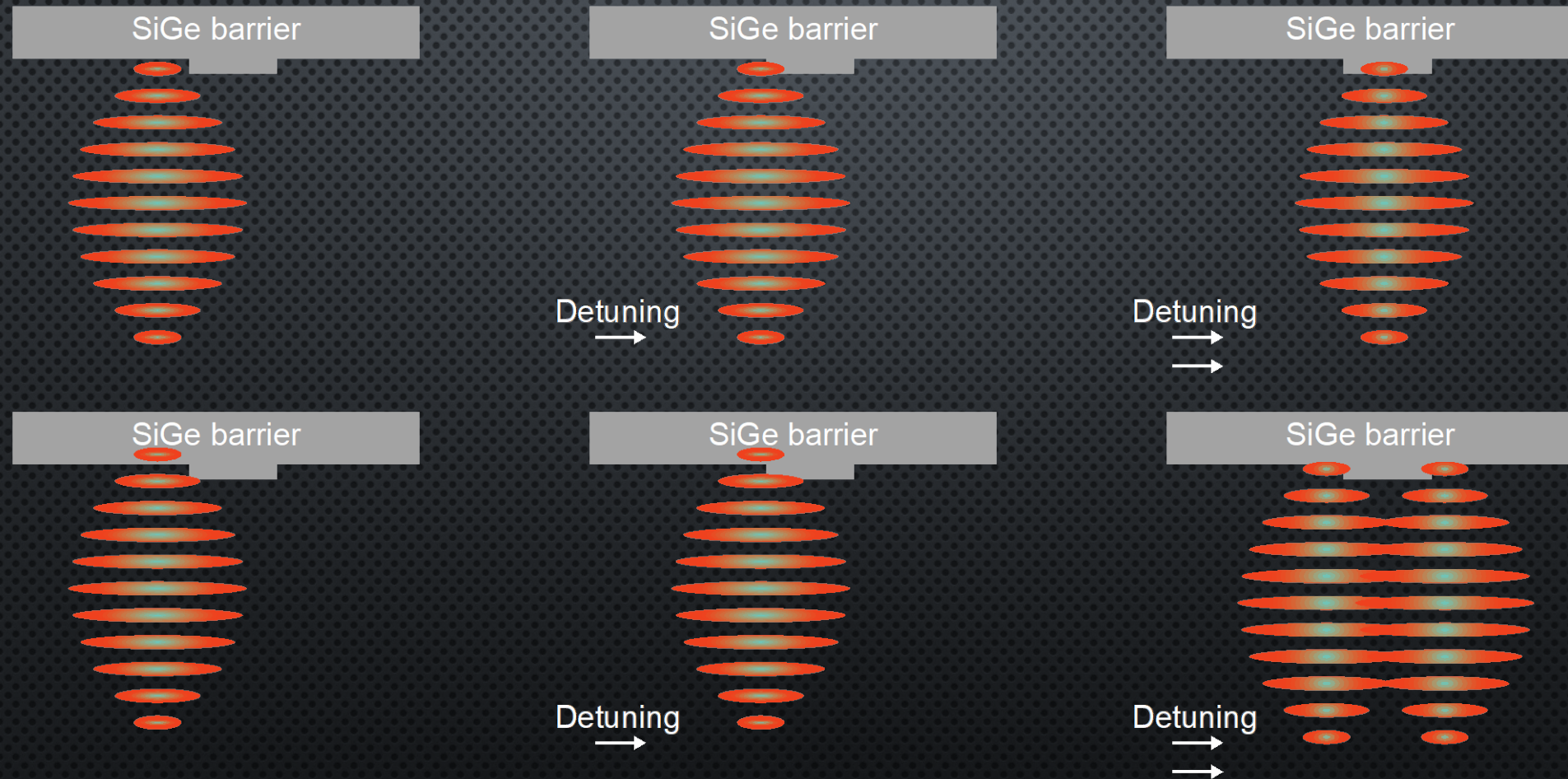


# VALLEY PHYSICS: ORIGINS AND IMPORTANCE



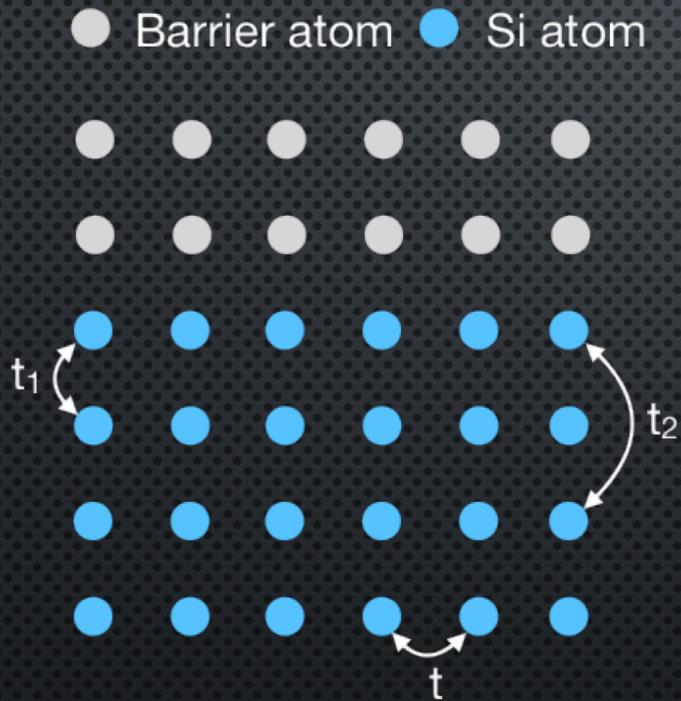


# DIFFERENT VALLEY STATES SEE THE INTERFACE IN A DIFFERENT WAY





# SIMULATING VALLEY PHYSICS WITH A SIMPLIFIED MODEL



- Minimal tight-binding that approximates the conduction band minima of Si
- The hopping parameters are chosen to reproduce the effective masses and CB minima position
- This simple model reproduces the behavior of valley splitting in the presence of fields, interfaces, disorder...

Details:

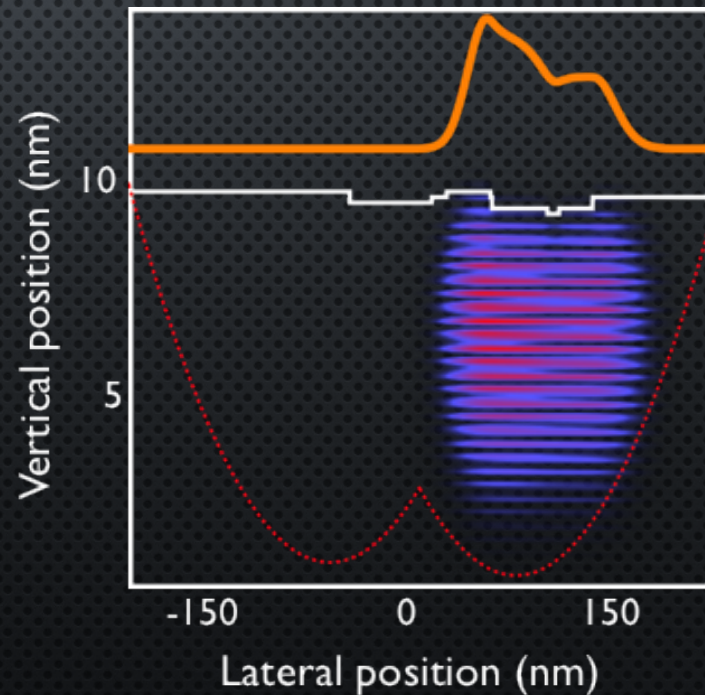
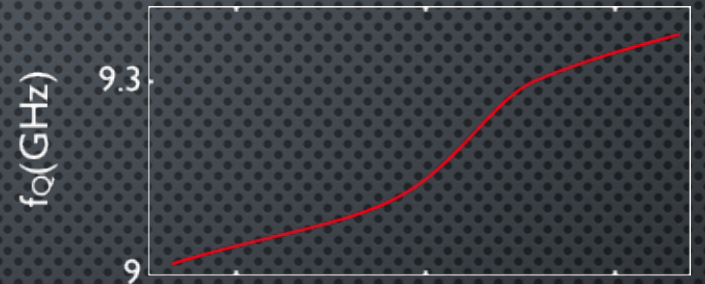
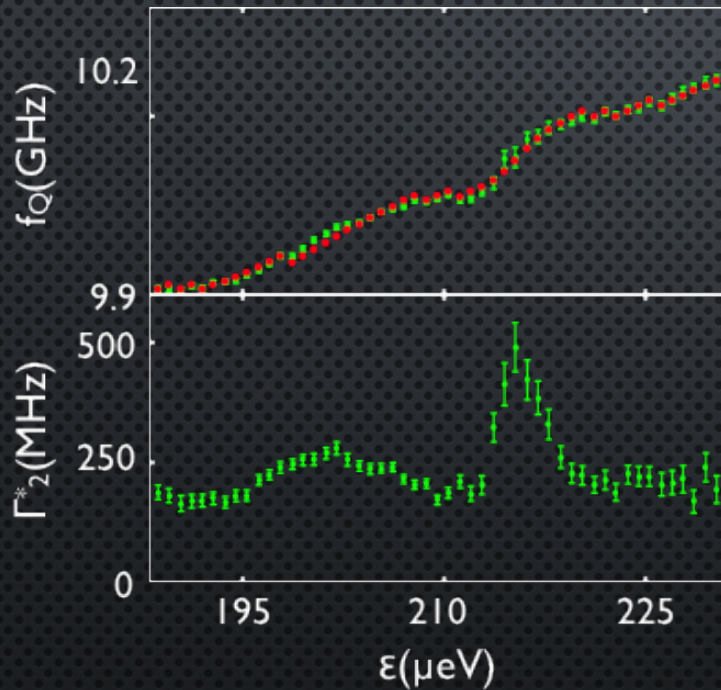
Boykin et al., APL 84, 115 (2004)

Abadillo-Uriel et al., Phys. Rev. B 98, 165438 (2018)



# SHARP CHANGES IN THE INTERFACE RESULT IN FASTER DECOHERENCE

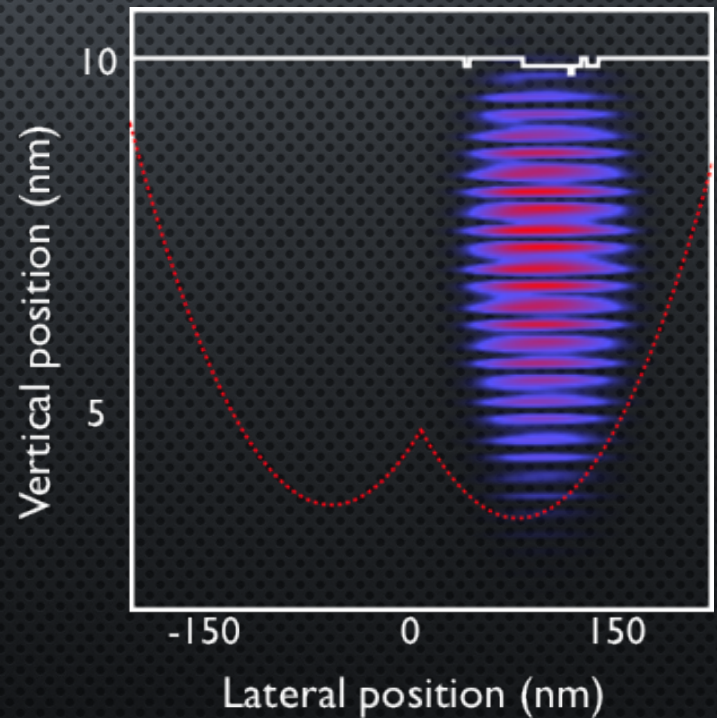
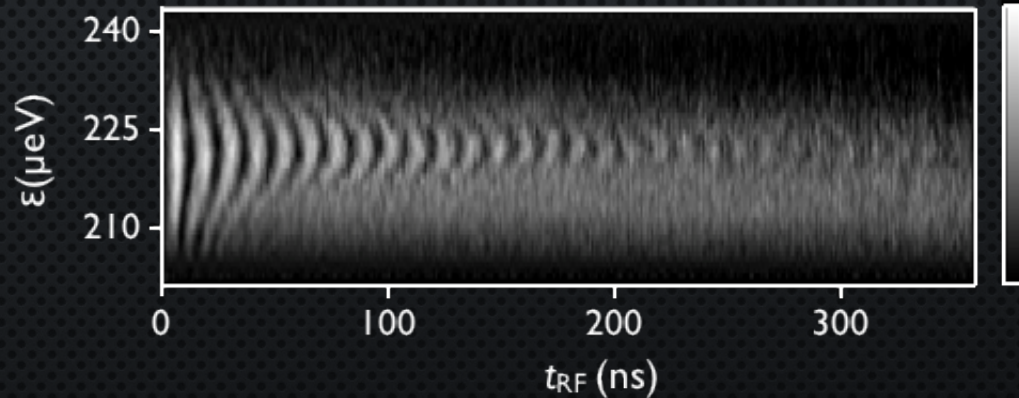
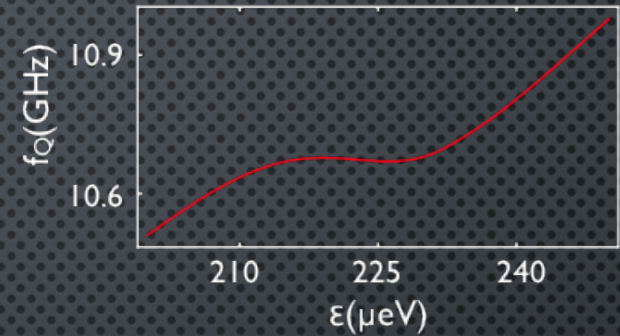
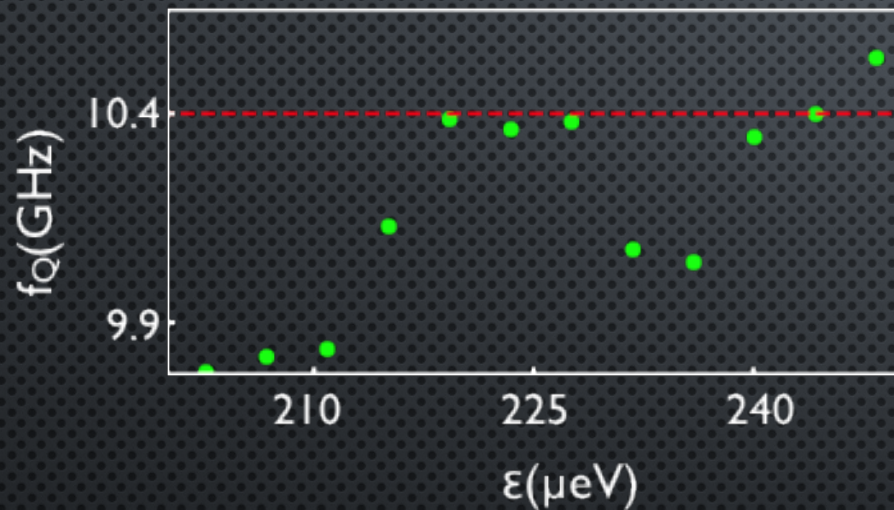
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Measurements from Brandur Thorgrimsson



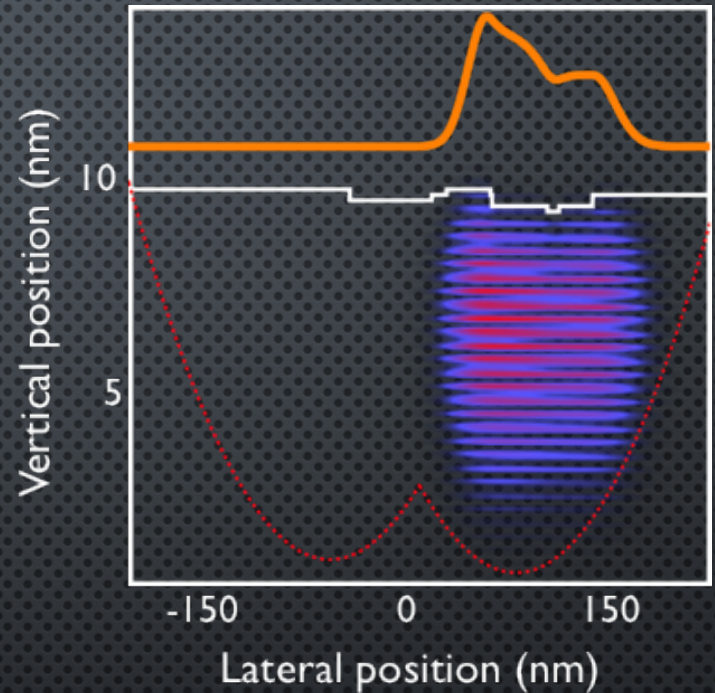
# INTERFACIAL DISORDER SLOWS DOWN THE ELECTRON EXTENDING THE COHERENCE





# CONCLUSIONS

- The material physics of Si has an impact in quantum computation
- Valley physics can be an asset
- With electric fields the disorder landscape of the electron can be changed: sweet spots appear in certain cases



# FUTURE WORK

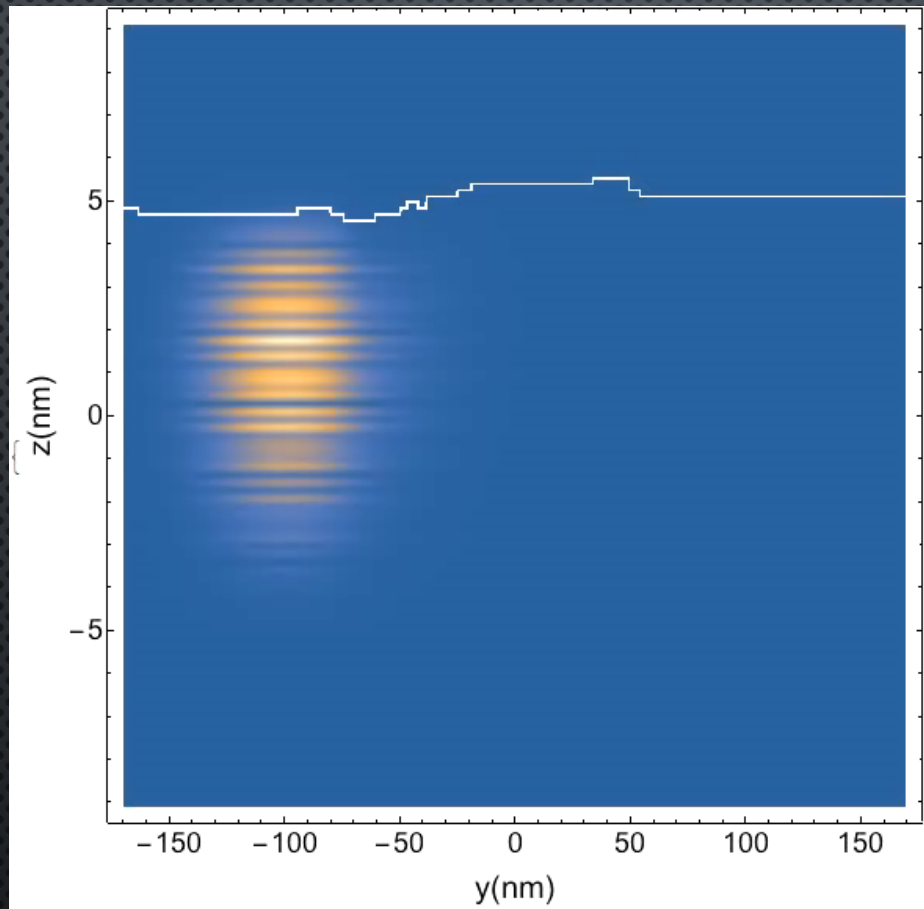
- Modifying the confinement potential
- e-e interactions



BACK UP  
SLIDES

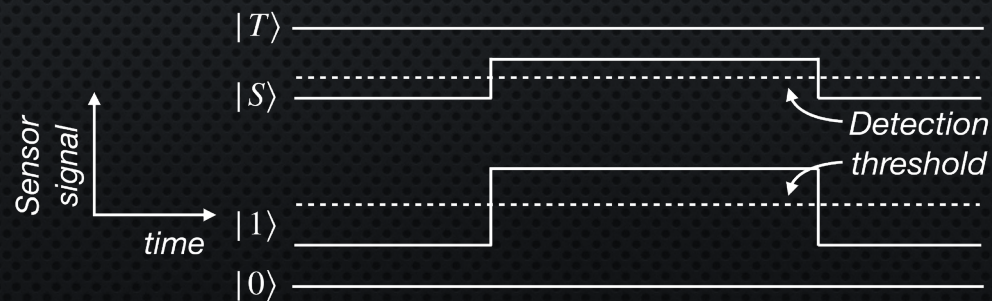
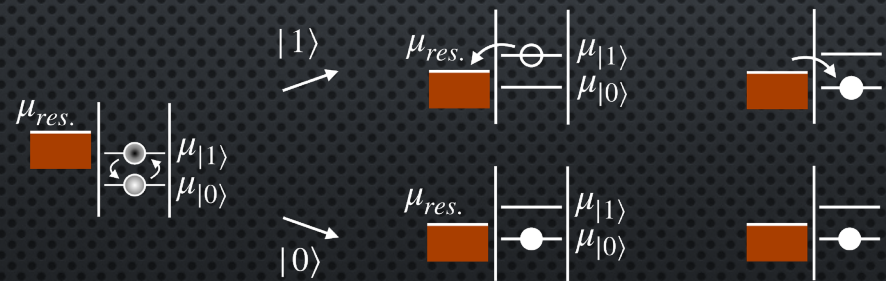
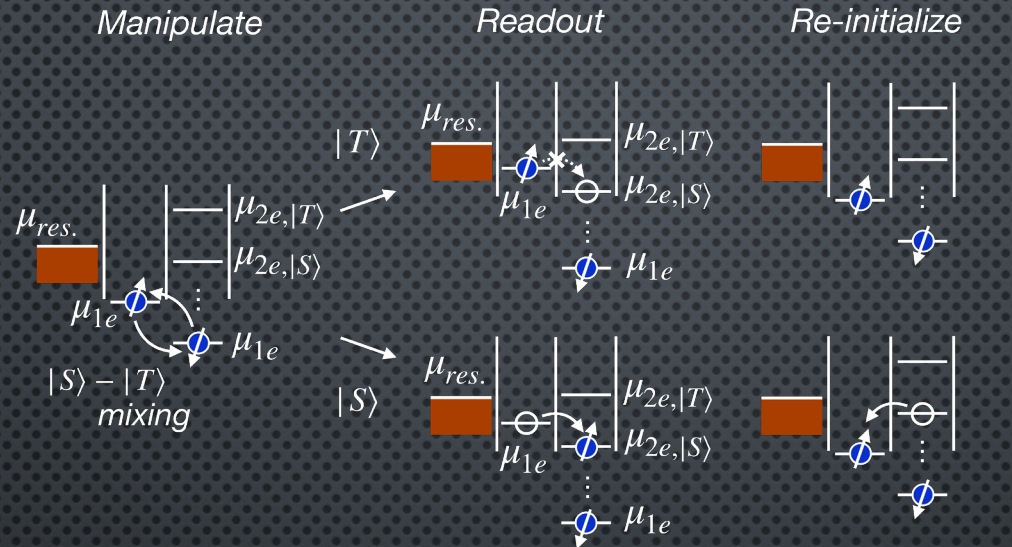


# EXAMPLE OF SUPER FAST BEHAVIOR



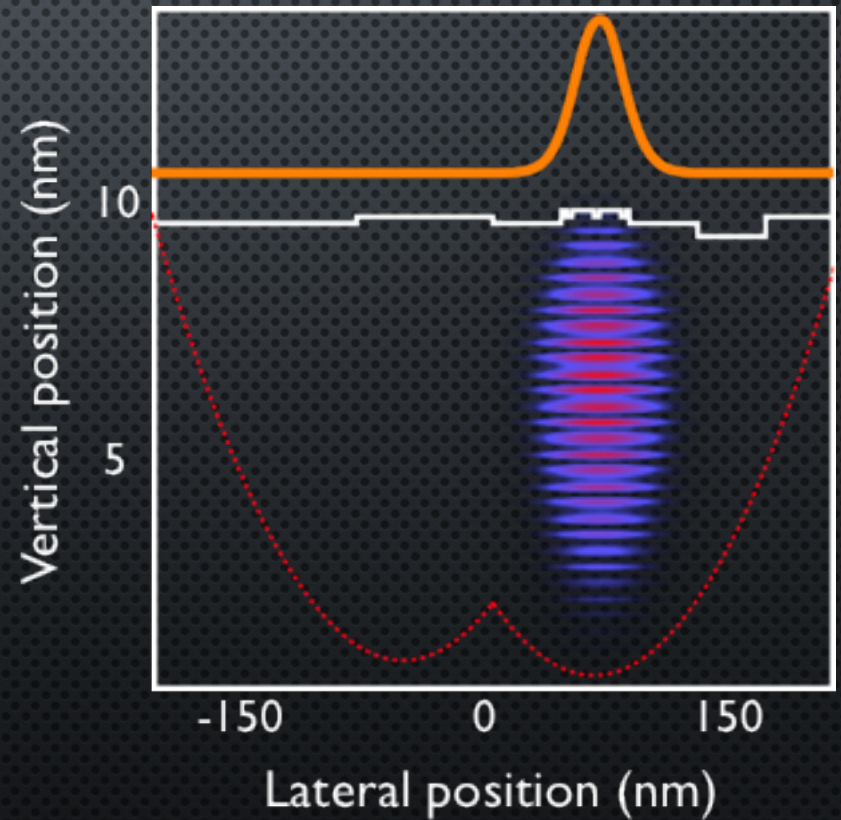
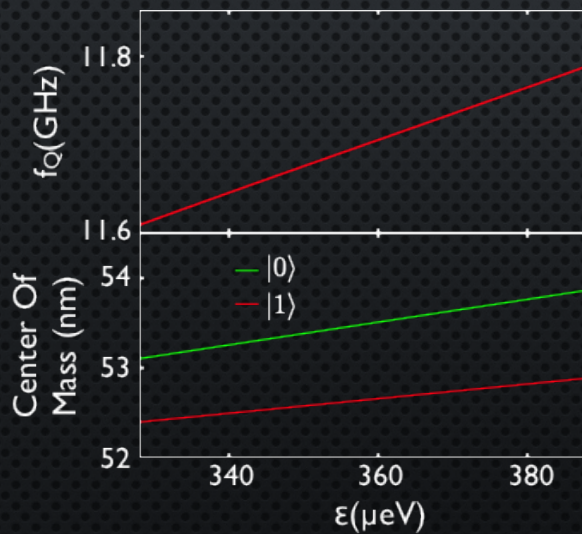
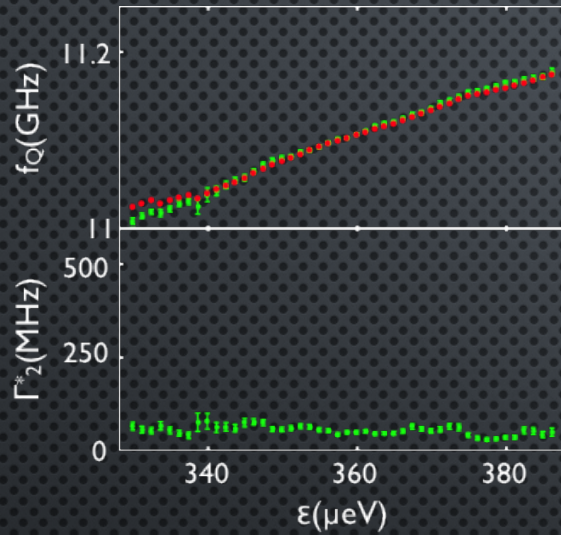


# READOUT MECHANISMS FOR QD QUBITS





# EXPECTED BEHAVIOR



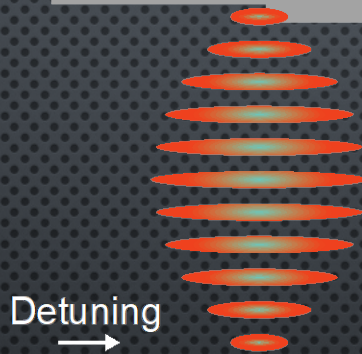


# VALLEY-ORBIT MECHANISMS

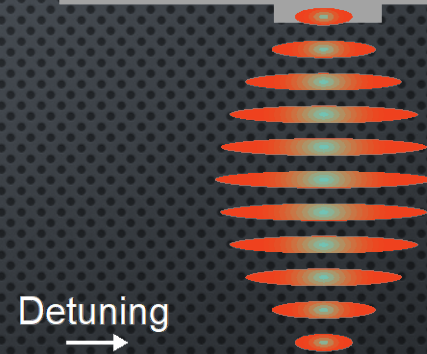
SiGe barrier



SiGe barrier



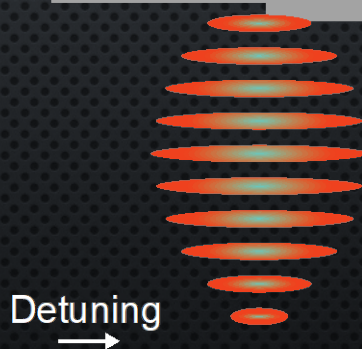
SiGe barrier



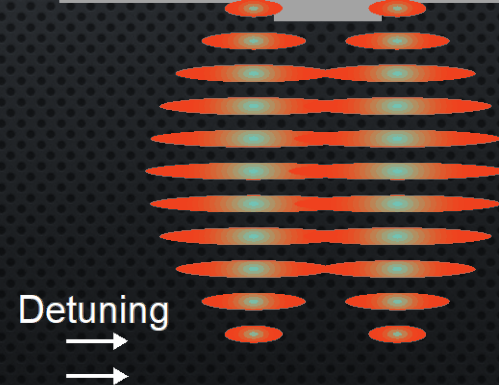
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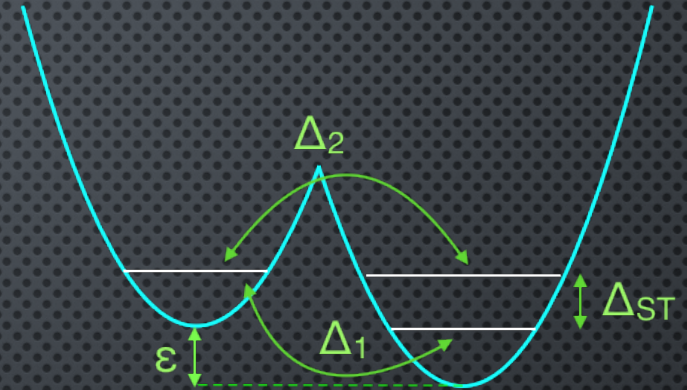
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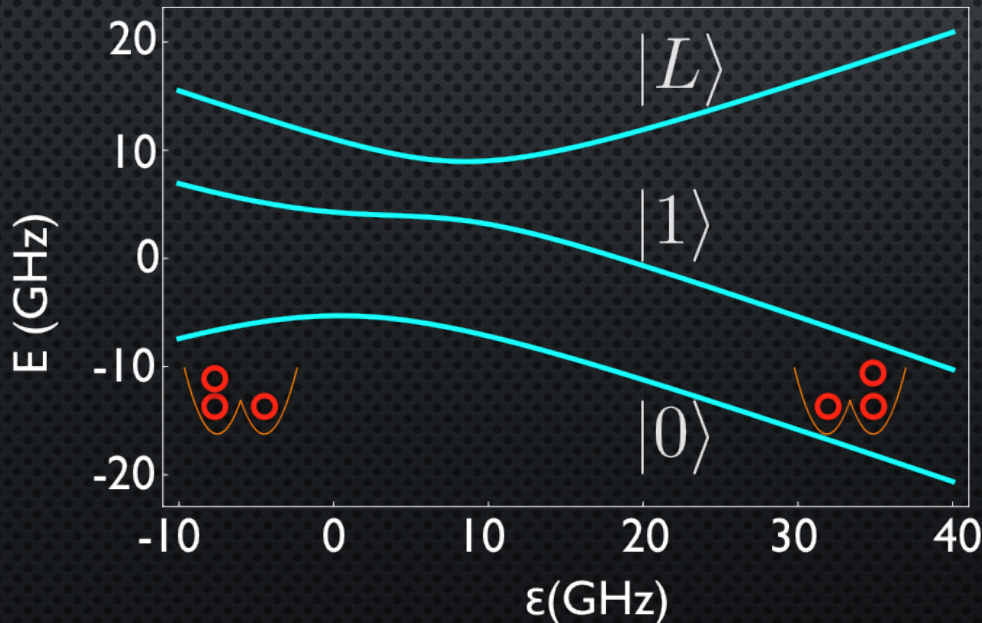


# IN DETAIL HYBRID QUBIT

$$H = \begin{pmatrix} -\varepsilon/2 & 0 & \Delta_1 \\ 0 & -\varepsilon/2 + \Delta_{ST} & \Delta_2 \\ \Delta_1 & \Delta_2 & \varepsilon/2 \end{pmatrix}$$



Energy diagram



Two anticrossings related to the qubit parameters

Far-detuned regime

Dipolar coupling maximized near the 1st anticrossing